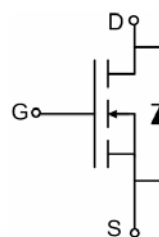
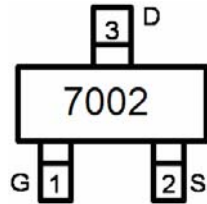



N-Channel Enhancement Mode Power MOSFET

<p>GENERAL FEATURES</p> <ul style="list-style-type: none"> ● $V_{DS} = 60V, I_D = 0.5A$ $R_{DS(ON)} < 3\Omega @ V_{GS}=5V$ $R_{DS(ON)} < 2\Omega @ V_{GS}=10V$ ● Lead free product is acquired ● Surface Mount Package <p>Application</p> <ul style="list-style-type: none"> ● Direct Logic-Level Interface: TTL/CMOS ● Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc. ● Battery Operated Systems ● Solid-State Relays 	 <p>Schematic diagram</p>  <p>Marking and pin Assignment</p>  <p>SOT-23 top view</p>
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Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
7002	HM7002	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D	0.5	A
	I_{DM}	0.8	A
Maximum Power Dissipation	P_D	0.2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	625	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60	68	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	µA

Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.7	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=5V, I_D=0.05A$	-	1.3	3	Ω
		$V_{GS}=10V, I_D=0.5A$	-	1.1	2	Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=0.2A$	0.08	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V,$ $F=1.0MHz$	-	20	50	PF
Output Capacitance	C_{oss}		-	10	20	PF
Reverse Transfer Capacitance	C_{rss}		-	3.6	5	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=0.2A$ $V_{GS}=10V, R_{GEN}=10\Omega$	-	10	-	nS
Turn-on Rise Time	t_r		-	50	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	17	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=0.5A,$ $V_{GS}=4.5V$	-	1.7	3	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=0.5A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	0.5	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

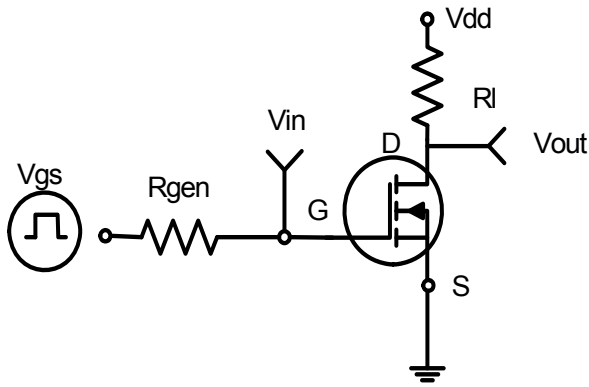


Figure 1: Switching Test Circuit

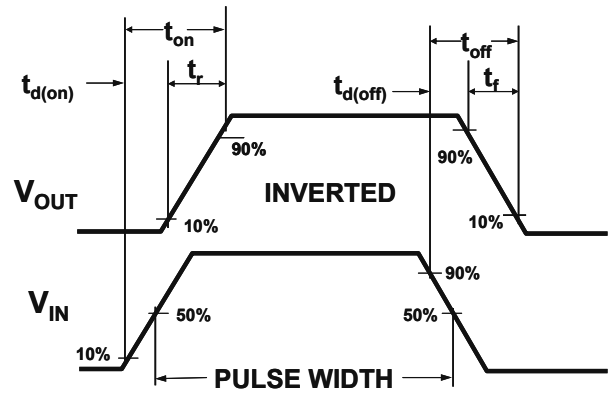


Figure 2: Switching Waveforms

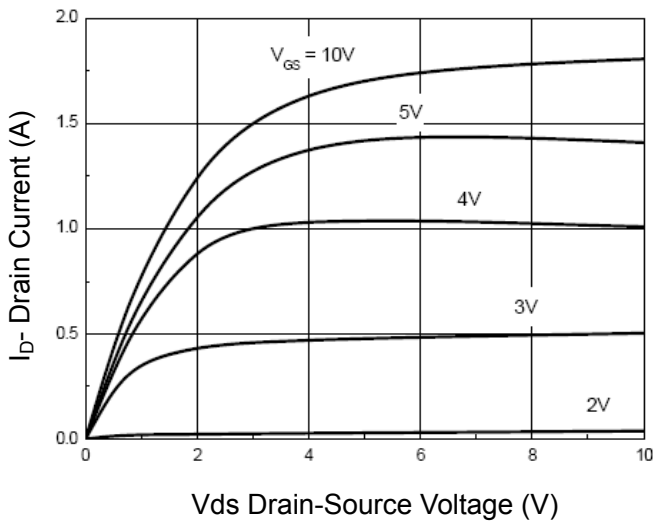


Figure 3 Output CHARACTERISTICS

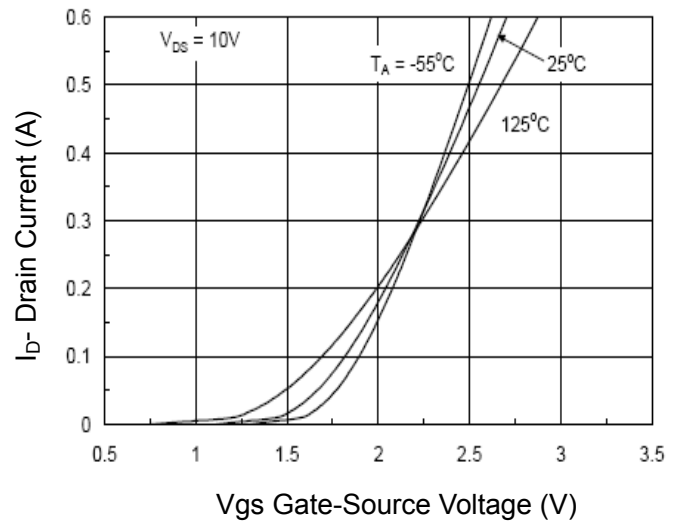


Figure 4 Transfer Characteristics

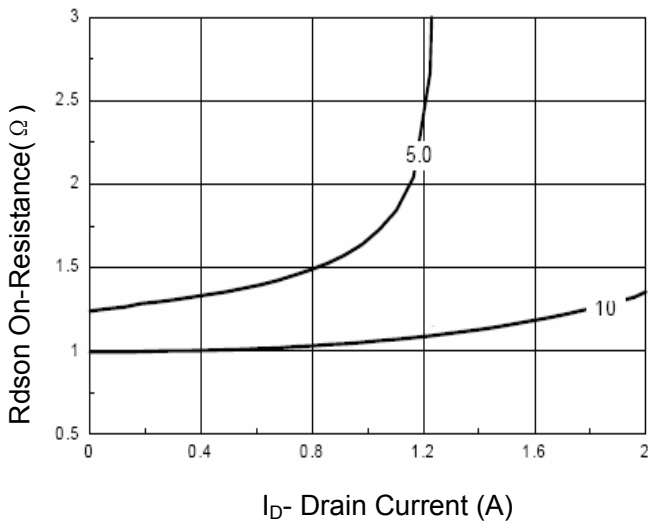


Figure 5 Drain-Source On-Resistance

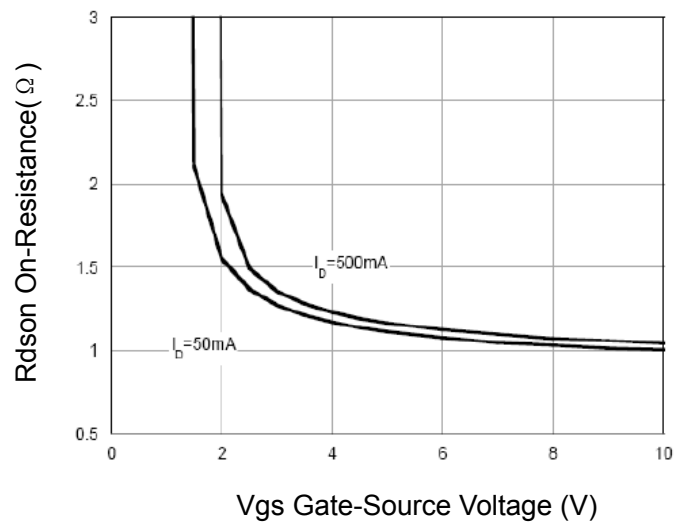


Figure 6 Rdson vs Vgs

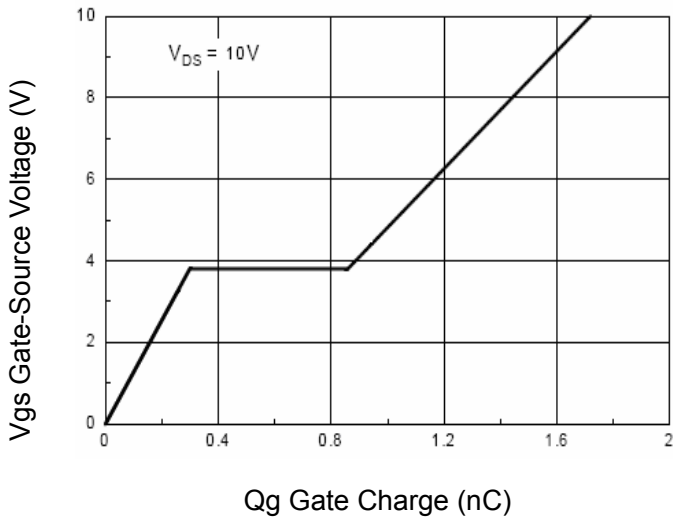


Figure 7 Gate Charge

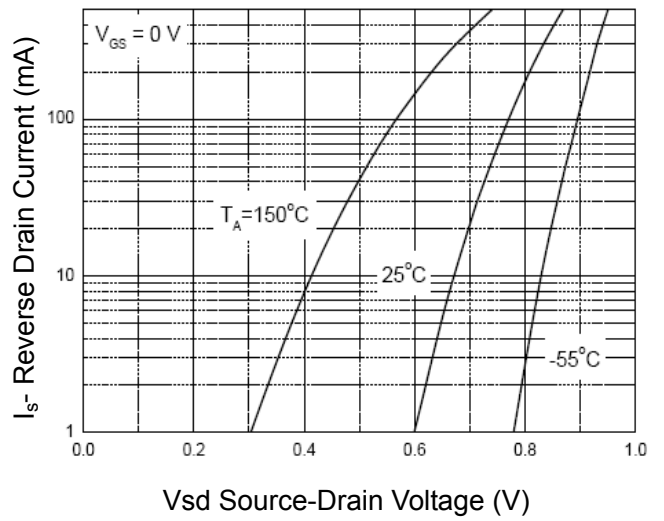


Figure 8 Source-Drain Diode Forward

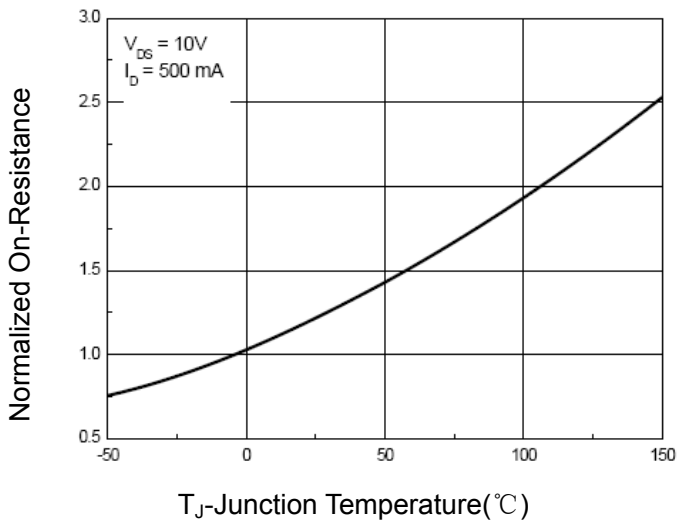


Figure 9 Drain-Source On-Resistance

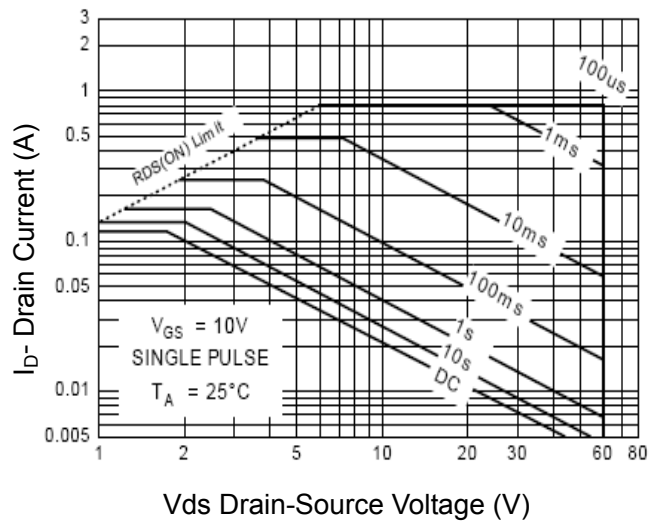


Figure 10 Safe Operation Area

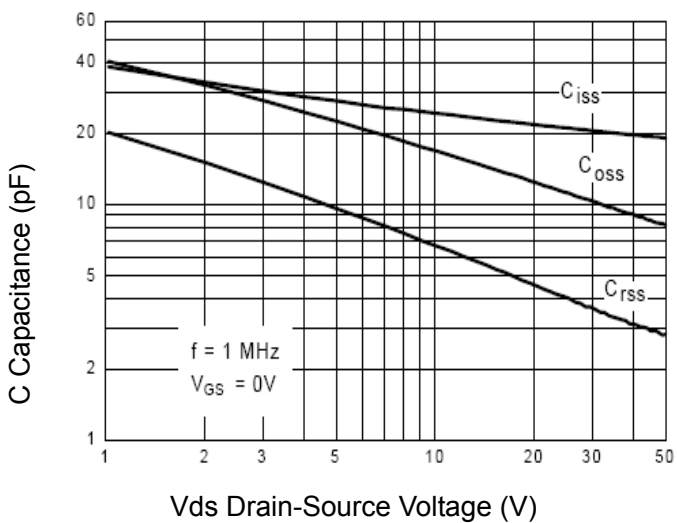


Figure 11 Capacitance vs Vds

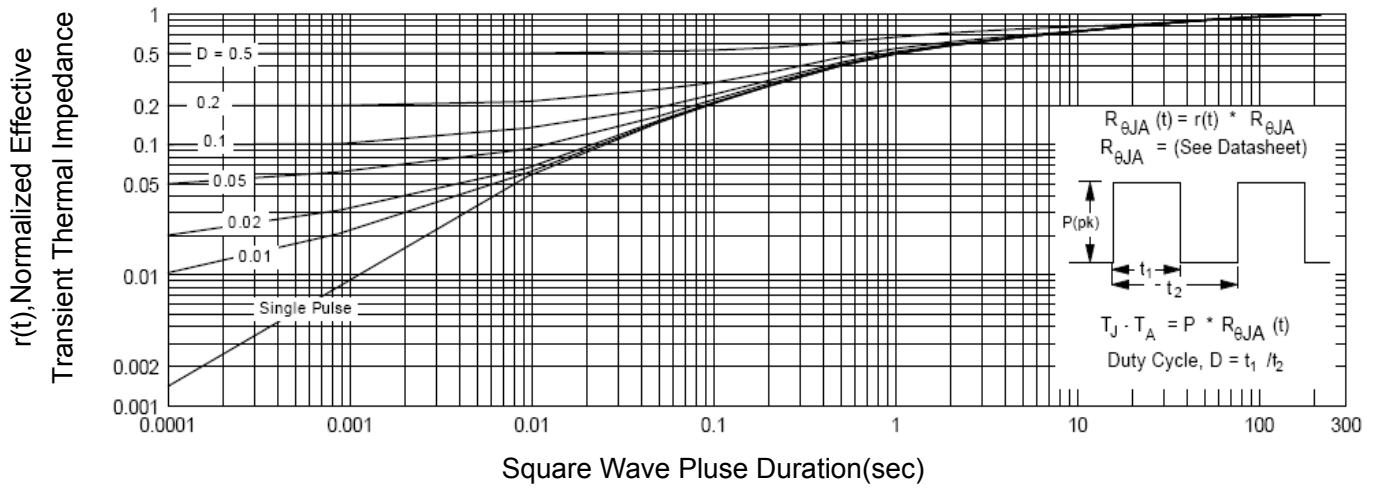
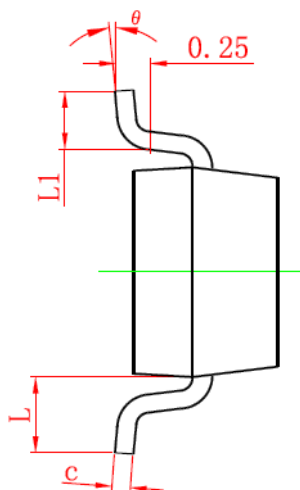
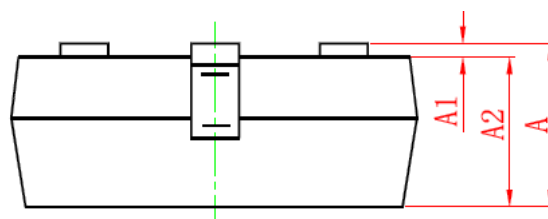
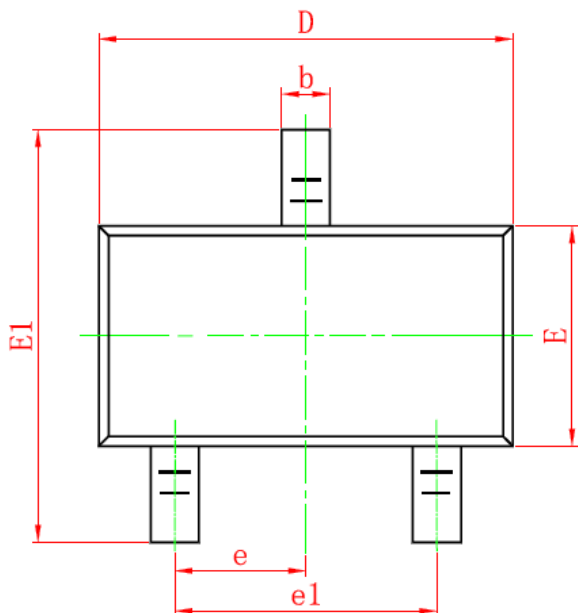


Figure 12 Normalized Maximum Transient Thermal Impedance

SOT-23 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT:mm)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

NOTES

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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